

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau



(43) International Publication Date
29 April 2004 (29.04.2004)

PCT

(10) International Publication Number
WO 2004/035858 A2

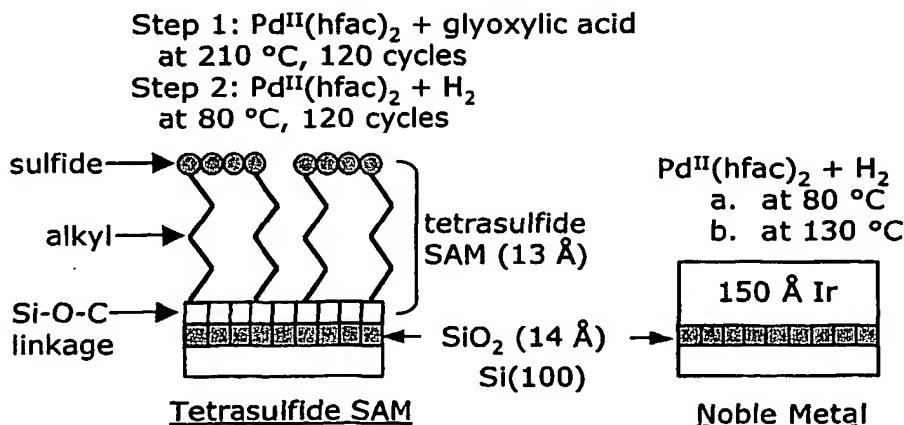
- (51) International Patent Classification⁷: C23C 16/00 (74) Agents: GIOENI, Mary, Louise et al.; Heslin Rothenberg Farley & Mesiti, 5 Columbia Circle, Albany, NY 12203 (US).
- (21) International Application Number: PCT/US2003/032644
- (22) International Filing Date: 15 October 2003 (15.10.2003)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
60/418,519 15 October 2002 (15.10.2002) US
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- (81) Designated States (national): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (regional): ARIPO patent (GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

- without international search report and to be republished upon receipt of that report

[Continued on next page]

(54) Title: ATOMIC LAYER DEPOSITION OF NOBLE METALS



WO 2004/035858 A2

(57) Abstract: The present invention relates to ALD processes for deposition of a metal selected from Pd, Rh, Ru, Pt and Ir wherein a layer including the metal is formed on a surface composed of a material selected from W, Ta, Cu, Ni, Co, Fe, Mn, Cr, V Nb, tungsten nitride, tantalum nitride, titanium nitride, dielectrics and activated dielectrics at a temperature ranging from >60°C to <260°C. The layer is formed by sequentially pulsing into a chamber containing said surface a precursor for the metal and a reducing gas selected from hydrogen, glyoxylic acid, oxalic acid, formaldehyde, 2-propanol, imidazole and plasma-activated hydrogen.